



UT110N08H

Preliminary

Power MOSFET

110A, 80V N-CHANNEL POWER MOSFET

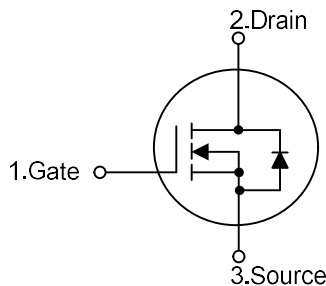
DESCRIPTION

The UTC **UT110N08H** is an N-channel enhancement mode Power MOSFET, it uses UTC's advanced technology to provide customers a minimum on-state resistance and high switching speed.

FEATURES

- * $R_{DS(ON)} \leq 5.5 \text{ m}\Omega$ @ $V_{GS} = 10\text{V}$, $I_D = 55\text{A}$
- * High switching speed
- * Improved dv/dt capability

SYMBOL



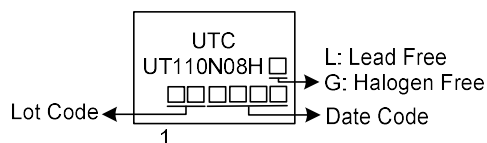
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UT110N08HL-TA3-T	UT110N08HG-TA3-T	TO-220	G	D	S	Tube
UT110N08HL-TQ2-T	UT110N08HG-TQ2-T	TO-263	G	D	S	Tube
UT110N08HL-TQ2-R	UT110N08HG-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

UT110N08HG-TA3-T	(1) Packing Type (2) Package Type (3) Green Package	(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TQ2: TO-263 (3) G: Halogen Free and Lead Free, L: Lead Free
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MARKING



■ **ABSOLUTE MAXIMUM RATINGS** ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DS}	80	V
Gate-Source Voltage		V_{GS}	± 20	V
Drain Current	Continuous	I_D	110	A
	Pulsed	I_{DM}	220	A
Avalanche Energy	Single Pulsed	E_{AS}	207	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	3.7	V/ns
Power Dissipation		P_D	215	W
Junction Temperature		T_J	+150	$^{\circ}\text{C}$
Storage Temperature Range		T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 0.1\text{mH}$, $I_{AS} = 64.4\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^{\circ}\text{C}$.

4. $I_{SD} \leq 30\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^{\circ}\text{C}$.

■ **THERMAL DATA (NOTE)**

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	62.5	$^{\circ}\text{C}/\text{W}$
Junction to Case	θ_{JC}	0.58 (Note)	$^{\circ}\text{C}/\text{W}$

Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

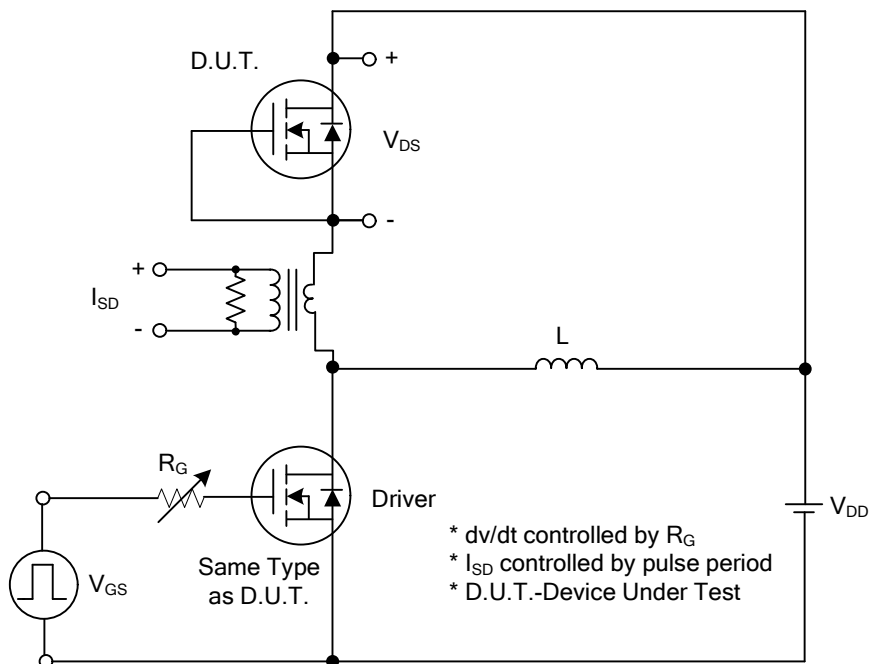
■ **ELECTRICAL CHARACTERISTICS** ($T_J=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =250μA, V _{GS} =0V	80			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =80V, V _{GS} =0V			1	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} =+20V, V _{DS} =0V			+100	nA
	Reverse		V _{GS} =-20V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	I _D =250μA, V _{DS} =V _{GS}	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =55A			5.5	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1MHz		9237		pF
Output Capacitance		C _{OSS}			734		pF
Reverse Transfer Capacitance		C _{RSS}			629		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q _G	V _{DD} =64V, V _{GS} =10V, I _D =110A, (Note 1, 2)		263		nC
Gate to Source Charge		Q _{GS}			59		nC
Gate to Drain Charge		Q _{GD}			118		nC
Turn-ON Delay Time		t _{D(ON)}	V _{DD} =40V, V _{GS} =10V I _D =110A, R _G =3Ω (Note 1, 2)		33		ns
Rise Time		t _R			30		ns
Turn-OFF Delay Time		t _{D(OFF)}			102		ns
Fall-Time		t _F			43		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				110	A
Drain-Source Diode Forward Voltage		V _{SD}	I _S =110A			1.4	V
Reverse Recovery Time		t _{rr}	I _S =30A, V _{GS} =0V		68		nS
Reverse Recovery Charge (Note 1)		Q _{rr}	dI _F /dt=100A/μs		134		nC

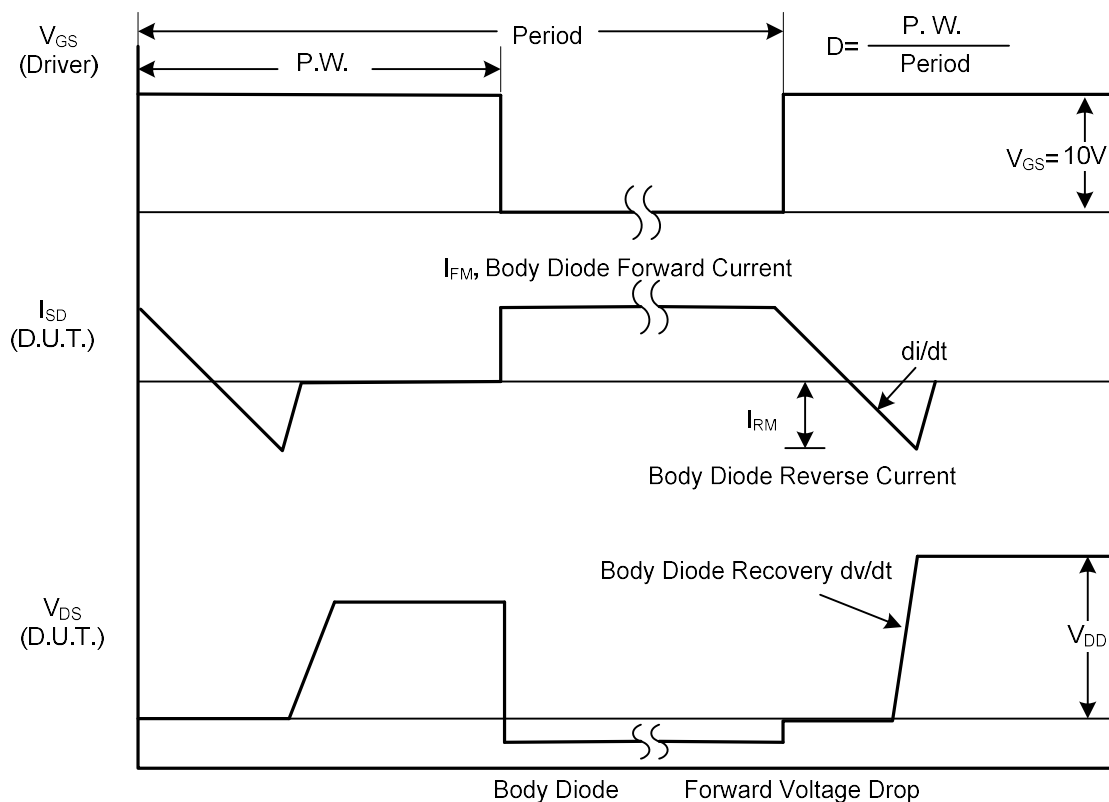
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating ambient temperature.

■ TEST CIRCUITS AND WAVEFORMS

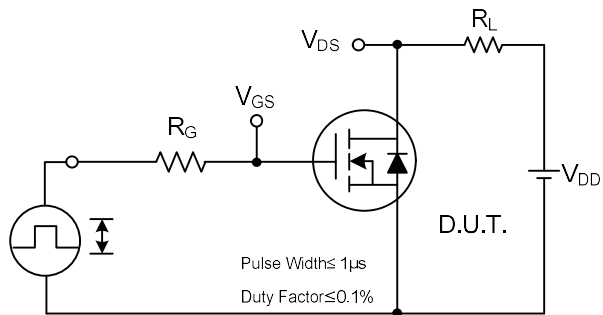


Peak Diode Recovery dv/dt Test Circuit

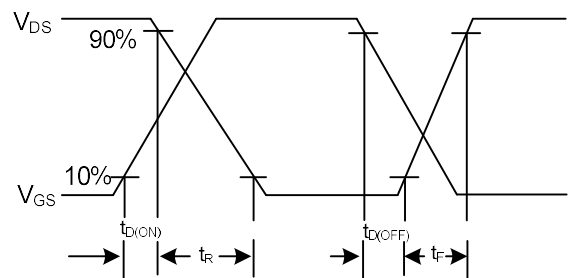


Peak Diode Recovery dv/dt Waveforms

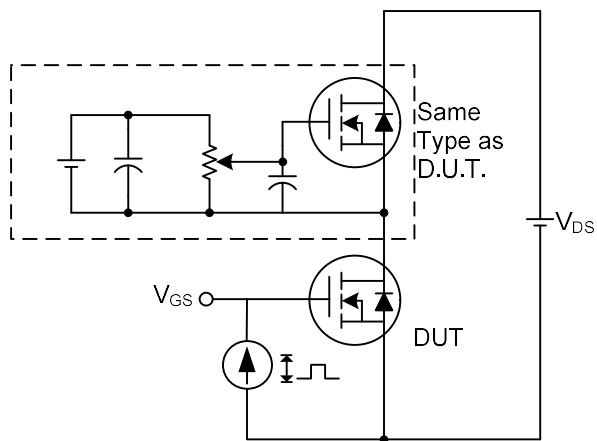
■ TEST CIRCUITS AND WAVEFORMS



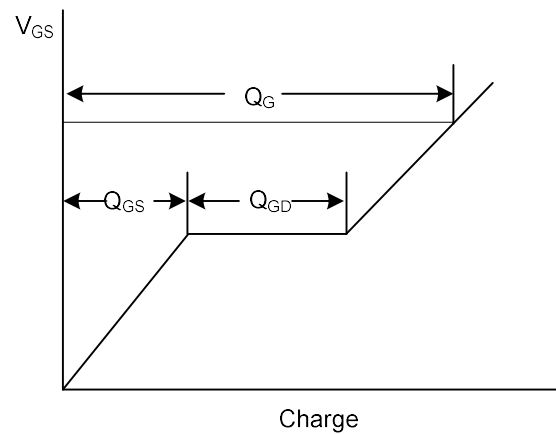
Switching Test Circuit



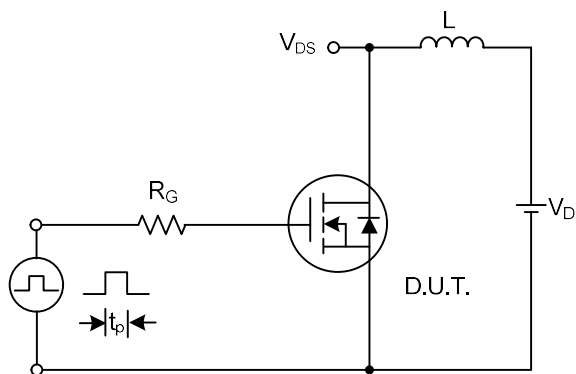
Switching Waveforms



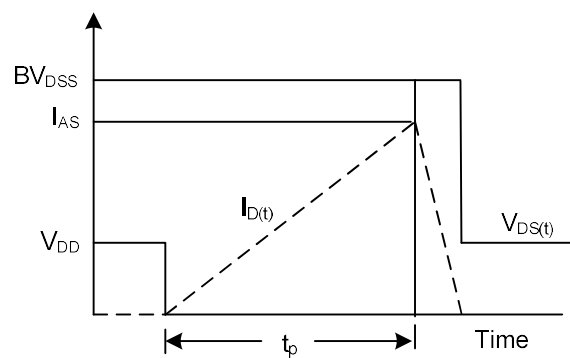
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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